

MS1261

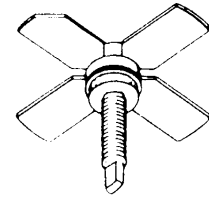
RF & MICROWAVE TRANSISTORS VHF MOBILE APPLICATIONS

Features

- 175 MHz
- 12.5 VOLTS
- P_{OUT} = 15 WATTS
- G_p = 12 dB MINIMUM
- INPUT IMPEDANCE MATCHING
- COMMON EMITTER CONFIGURATION

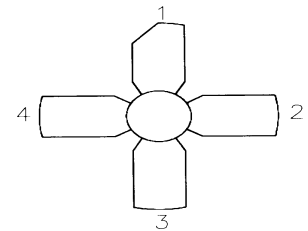
DESCRIPTION:

The MS1261 is a Class C 12.5V epitaxial silicon NPN planar transistor designed primarily for UHF communications. This device utilizes a gold metallized, emitter ballasted die geometry for superior reliability and infinite VSWR capability.



.280 4L STUD (M122)
epoxy sealed

PIN CONNECTION



1. Collector 3. Base
2. Emitter 4. Emitter

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	36	V
V _{CEO}	Collector-Emitter Voltage	18	V
V _{CES}	Collector-Emitter Voltage	36	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Device Current	2.5	A
P _{DISS}	Power Dissipation	34	W
T _J	Junction Temperature	+200	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Thermal Data

R _{TH(J-C)}	Thermal Resistance Junction-case	8.75	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV_{CES}	$I_C = 50 \text{ mA}$ $V_{BE} = 0V$	36	---	---	V
BV_{CEO}	$I_C = 15 \text{ mA}$	18	---	---	V
BV_{EBO}	$I_E = 2.5 \text{ mA}$ $I_C = 0\text{mA}$	4.0	---	---	V
I_{CBO}	$V_{CE} = 15 \text{ V}$ $I_E = 0\text{mA}$	---	---	1	mA
H_{FE}	$V_{CE} = 5 \text{ V}$ $I_C = 250\text{mA}$	20	---	200	---

DYNAMIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
P_{OUT}	$f = 175 \text{ MHz}$ $P_{IN} = 1W$ $V_{CE} = 12.5V$	15	---	---	W
η_c	$f = 175 \text{ MHz}$ $P_{IN} = 1W$ $V_{CE} = 12.5V$	60	---	---	%
G_P	$f = 175 \text{ MHz}$ $P_{IN} = 1W$ $V_{CE} = 12.5V$	12	---	---	dB
C_{OB}	$f = 1 \text{ MHz}$ $V_{CB} = 12.5V$	---	---	45	pf

IMPEDANCE DATA

FREQ	$Z_{IN}(\Omega)$	$Z_{CL}(\Omega)$
175 MHz	$1.2 - j0.4$	$5.2 + j1.1$

$P_{OUT} = 15W$
 $V_{CC} = 12.5V$

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PACKAGE MECHANICAL DATA

